

COMPLEMENTARY SILICON DARLINGTON POWER TRANSISTORS





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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6298 series devices are complementary silicon Darlington power transistors manufactured by the epitaxial base process designed for high gain amplifier and medium speed switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T _C =25°C) Collector-Base Voltage	SYMBOL V _{CBO}	2N6298 2N6300 60	2N6299 2N6301 80	
Collector-Emitter Voltage	VCEO	60	80	v
Emitter-Base Voltage	V _{EBO}	5	.0	V
Continuous Collector Current	IC	8	.0	А
Peak Collector Current	ICM	1	6	А
Continuous Base Current	۱ _B	12	20	mA
Power Dissipation	PD	7	5	W
Operating and Storage Junction Temperature	TJ, Tstg	-65 to	+200	°C
Thermal Resistance	Θ^{JC}	2.	33	°C/W

	50						
ELECTRICAL CHARACTERISTICS: (T _C =25°C unless otherwise noted)							
SYMBOL	TEST CONDITIONS	MIN	MAX				
ICEV	V _{CE} =Rated V _{CEO} , V _{BE} =1.5V		0.5				
ICEV	V _{CE} =Rated V _{CEO} , V _{BE} =1.5V, T _C =150°C		5.0				
ICEO	V _{CE} =½Rated V _{CEO}		0.5				
IEBO	V _{EB} =5.0V		2.0				
BVCEO	I _C =100mA (2N6298, 2N6300)	60					
BVCEO	I _C =100mA (2N6299, 2N6301)	80					
V _{CE(SAT)}	I _C =4.0A, I _B =16mA		2.0				
V _{CE(SAT)}	I _C =8.0A, I _B =80mA		3.0				
V _{BE(SAT)}	I _C =8.0A, I _B =80mA		4.0				
V _{BE(ON)}	V _{CE} =3.0V, I _C =4.0A		2.8				
h _{FE}	V _{CE} =3.0V, I _C =4.0A	750	18K				
h _{FE}	V _{CE} =3.0V, I _C =8.0A	100					

 hfe
 V_{CE}=3.0V, I_C=3.0A, f=1.0kHz
 300

 fT
 V_{CE}=3.0V, I_C=3.0A, f=1.0MHz
 4.0
 MHz

 C_{ob}
 V_{CB}=10V, I_E=0, f=100kHz (NPN types)
 200
 pF

 C_{ob}
 V_{CB}=10V, I_E=0, f=100kHz (PNP types)
 300
 pF

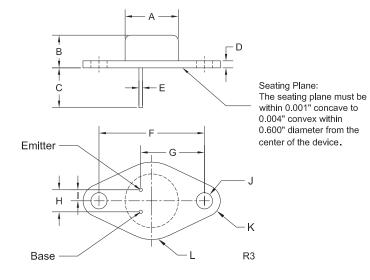
R3 (2-September 2014)

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COMPLEMENTARY SILICON DARLINGTON POWER TRANSISTORS

TO-66 CASE - MECHANICAL OUTLINE



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
A (DIA)	0.470	0.500	11.94	12.70			
В	0.250	0.340	6.35	8.64			
С	0.360	-	9.14	-			
D	0.050	0.075	1.27	1.91			
E (DIA)	0.028	0.034	0.71	0.86			
F	0.956	0.964	24.28	24.48			
G	0.570	0.590	14.48	14.99			
Н	0.190	0.210	4.83	5.33			
	0.093	0.107	2.36	2.72			
J (DIA)	0.142	0.152	3.61	3.86			
K (RAD)	0.141		3.58				
L (RAD)	0.345		8.	76			
TO-66 (REV:R3)							

MARKING: FULL PART NUMBER

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OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- · Environmental regulation compliance
- Customer specific screening
- · Up-screening capabilities

· Custom product packing

Custom bar coding for shipments

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

REQUESTING PRODUCT PLATING

- If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when 1. ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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